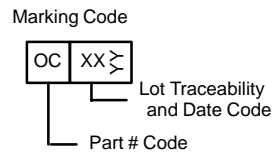
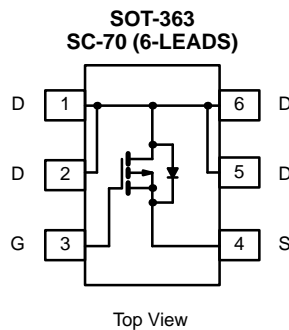




P-Channel 1.8-V (G-S) MOSFET

TrenchFET[®]
Power MOSFETs
1.8-V Rated

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.130 @ $V_{GS} = -4.5$ V	-1.8
	0.170 @ $V_{GS} = -2.5$ V	-1.5
	0.225 @ $V_{GS} = -1.8$ V	-1.3



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-12		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-1.8	-1.6	A
		$T_A = 85^\circ\text{C}$	-1.4	-1.2	
Pulsed Drain Current	I_{DM}	-5			
Continuous Diode Current (Diode Conduction) ^a	I_S	-0.8	-0.8		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	0.625	0.568	W
		$T_A = 85^\circ\text{C}$	0.400	0.295	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 5$ sec	165	200	$^\circ\text{C/W}$
		Steady State	180	220	
Maximum Junction-to-Foot (Drain)	R_{thJF}	105	130		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

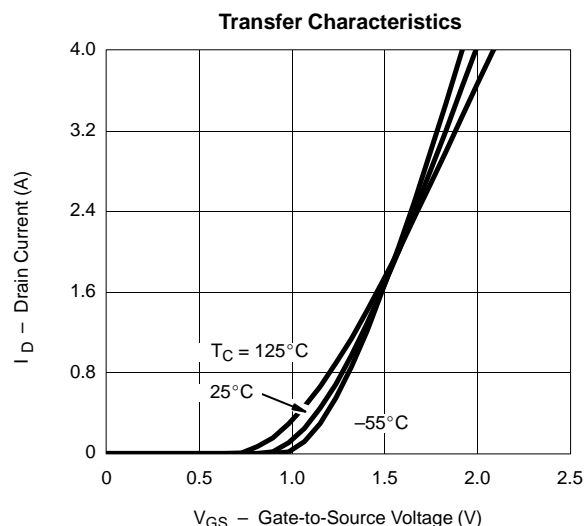
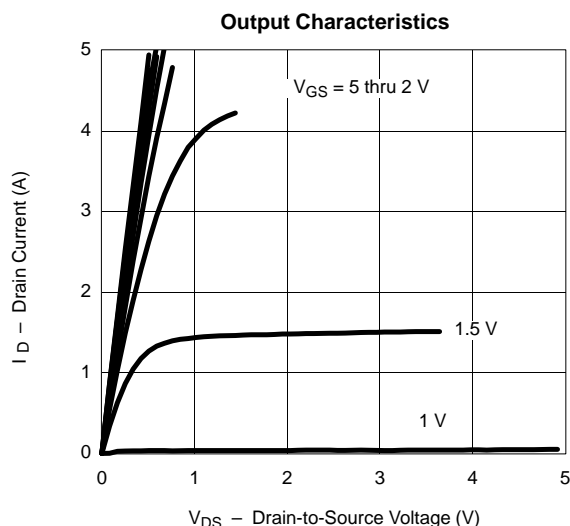


SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -9.6 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -9.6 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -4.5 V	-2			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -1.8 A		0.105	0.130	Ω
		V _{GS} = -2.5 V, I _D = -1.5 A		0.140	0.170	
		V _{GS} = -1.8 V, I _D = -0.8 A		0.185	0.225	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -1.8 A		4.3		S
Diode Forward Voltage ^a	V _{SD}	I _S = -0.8 A, V _{GS} = 0 V		-0.77	-1.1	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -6 V, V _{GS} = -4.5 V, I _D = -1.8 A		5.5	7.0	nC
Gate-Source Charge	Q _{gs}			0.95		
Gate-Drain Charge	Q _{gd}			1.10		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		8	12	ns
Rise Time	t _r			33	50	
Turn-Off Delay Time	t _{d(off)}			32	50	
Fall Time	t _f			29	45	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -0.8 A, di/dt = 100 A/μs		20	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

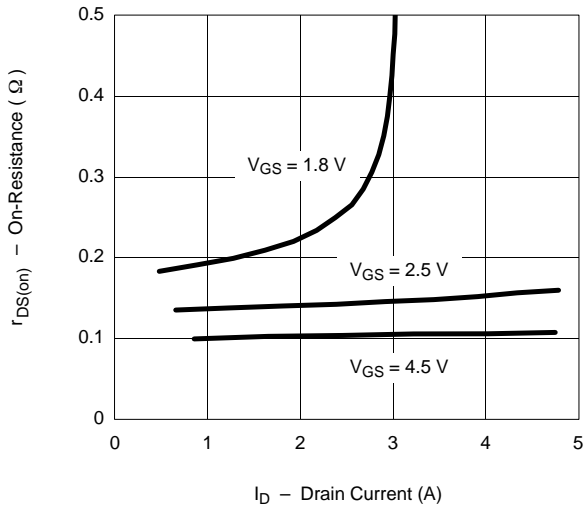
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



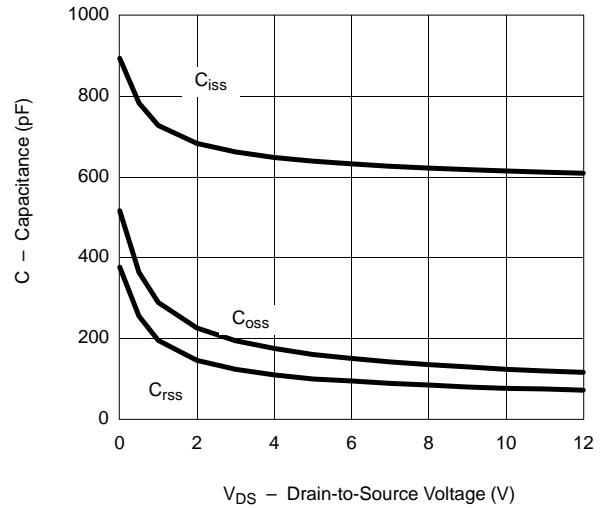


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

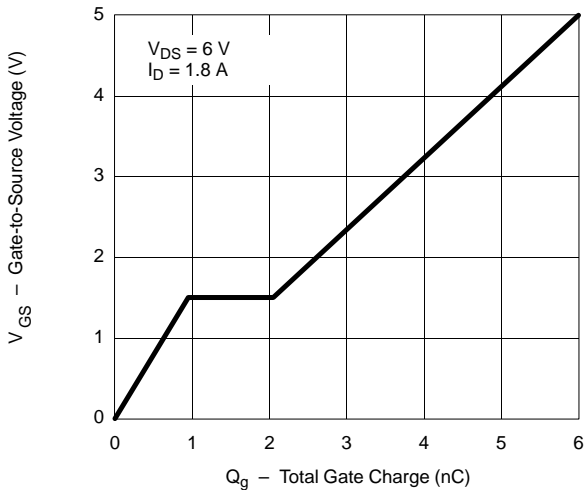
On-Resistance vs. Drain Current



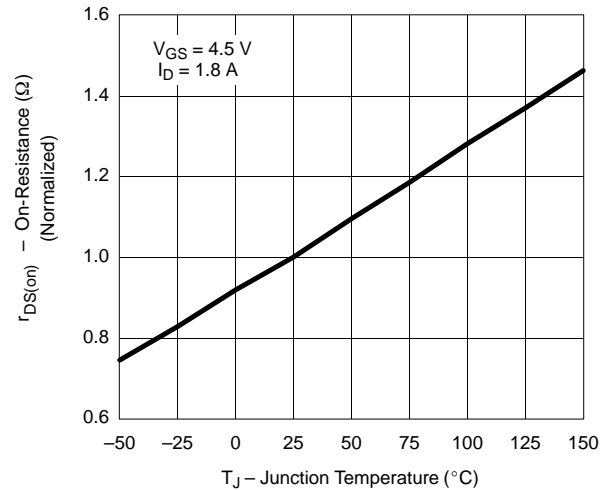
Capacitance



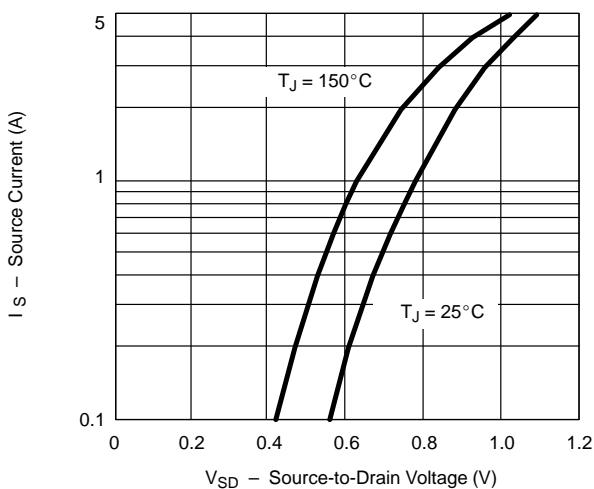
Gate Charge



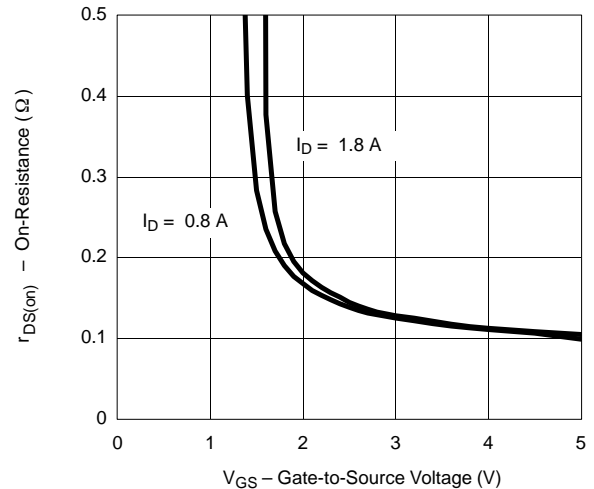
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

